PNP General Purpose Transistor

The MMBT2907AM3T5G device is a spin-off of our popular SOT-23 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-723 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- Reduces Board Space
- This is a Halide-Free Device
- This is a Pb-Free Device

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-60	Vdc
Collector - Base Voltage	V _{CBO}	-60	Vdc
Emitter - Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	-600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	265 2.1	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	470	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T _A = 25°C Derate above 25°C	P _D	640 5.1	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	195	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

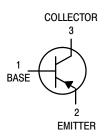
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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MARKING DIAGRAM



SOT-723 CASE 631AA STYLE 1



AC M Specific Device CodeDate Code

ORDERING INFORMATION

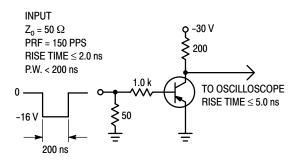
Device	Package	Shipping [†]
MMBT2907AM3T5G	SOT-723 (Pb-Free)	

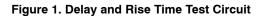
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS		.		•	I
Collector-Emitter Breakdown Voltage (Note 3) $(I_C = -10 \text{ mAdc}, I_B = 0)$		V _{(BR)CEO}	-60	-	Vdc
Collector – Base Breakdown Voltage ($I_C = -10 \mu Adc$, $I_E = 0$)		V _{(BR)CBO}	-60	-	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \mu Adc, I_C = 0$)		V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)		I _{CEX}	-	-50	nAdc
Collector Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -50 \text{ Vdc}, I_E = 0, T_A = 125^{\circ}\text{C})$	Ісво	- -	-0.010 -10	μAdc	
Base Cutoff Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)	I _{BL}	-	-50	nAdc	
ON CHARACTERISTICS					
DC Current Gain $ \begin{array}{l} (I_C = -0.1 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -150 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -500 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \end{array} $		h _{FE}	75 100 100 100 50	- - - 300 -	-
Collector – Emitter Saturation Voltage (Note 3) ($I_C = -150 \text{ mAdc}$, $I_B = -15 \text{ mAdc}$) (Note 3) ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)				-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (Note 3) ($I_C = -150 \text{ mAdc}$, $I_B = -15 \text{ mAdc}$) ($I_C = -500 \text{ mAdc}$, $I_B = -50 \text{ mAdc}$)			-	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS		-		•	II.
Current – Gain – Bandwidth Product (Notes 3, 4) (I _C = –50 mAdc, V _{CE} = –20 Vdc, f = 100 MHz)		f _T	200	-	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)			-	8.0	pF
Input Capacitance (V _{EB} = -2.0 Vdc, I _C = 0, f = 1.0 MHz)			-	30	
SWITCHING CHARACTERISTICS		•	•	•	•
Turn-On Time		t _{on}	-	45	
Delay Time	$(V_{CC} = -30 \text{ Vdc}, I_{C} = -150 \text{ mAdc}, I_{B1} = -15 \text{ mAdc})$	t _d	-	10	
Rise Time	.51 .5	t _r	-	40]
Turn-Off Time		t _{off}	-	100	ns
Storage Time	$(V_{CC} = -6.0 \text{ Vdc}, I_C = -150 \text{ mAdc}, I_{B1} = I_{B2} = -15 \text{ mAdc})$		-	80	
Fall Time	-01 -02,	t _f	-	30	

- 3. Pulse Test: Pulse Width \leq 300 $\mu s,$ Duty Cycle \leq 2.0%. 4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.





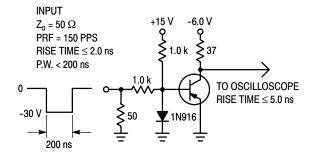


Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

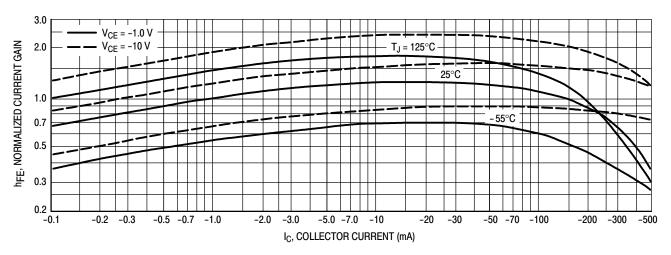


Figure 3. DC Current Gain

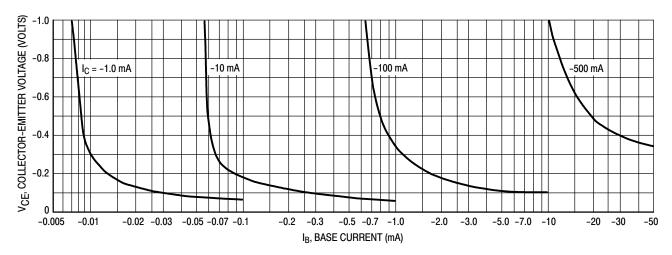


Figure 4. Collector Saturation Region

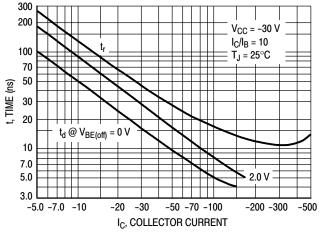


Figure 5. Turn-On Time

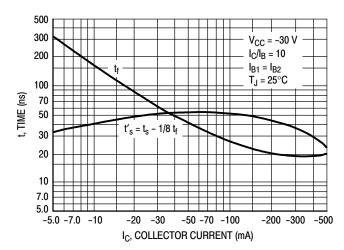
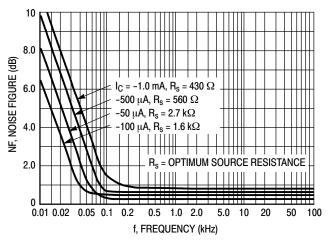


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL Characteristics NOISE FIGURE

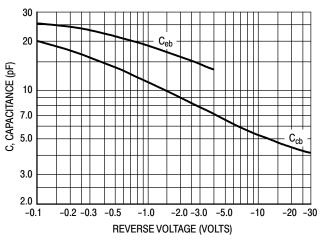
 V_{CE} = 10 Vdc, T_A = 25°C



8.0 NF, NOISE FIGURE (dB) 6.0 I_C = -50 μA -100 μA -500 μA 4.0 2.0 100 200 2.0 k 5.0 k 10 k 20 k 50 k 50 1.0 k R_s, SOURCE RESISTANCE (OHMS)

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects



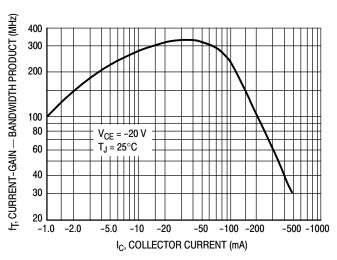
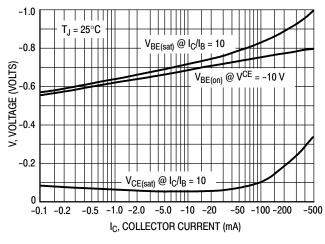


Figure 9. Capacitances

Figure 10. Current-Gain - Bandwidth Product



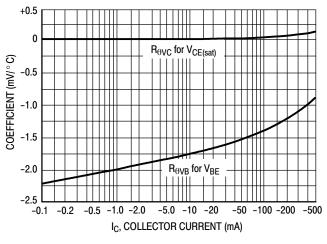
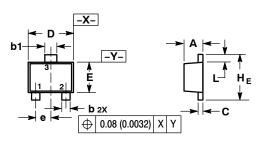


Figure 11. "On" Voltage

Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

SOT-723 CASE 631AA-01 **ISSUE C**



STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

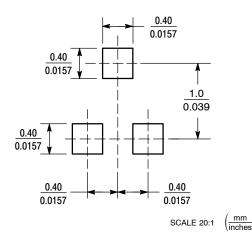
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

 DIMENSIONS D AND E DO NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.45	0.50	0.55	0.018	0.020	0.022
b	0.15	0.21	0.27	0.0059	0.0083	0.0106
b1	0.25	0.31	0.37	0.010	0.012	0.015
С	0.07	0.12	0.17	0.0028	0.0047	0.0067
D	1.15	1.20	1.25	0.045	0.047	0.049
E	0.75	0.80	0.85	0.03	0.032	0.034
е	0.40 BSC			0.016 BSC		
ΗE	1.15	1.20	1.25	0.045	0.047	0.049
L	0.15	0.20	0.25	0.0059	0.0079	0.0098

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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